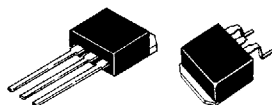


2SJ268



2093

2090

LD (Low Drive) Series $V_{DS} = 60V$

P Channel Power MOSFET

Ⓔ4237

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Surface mount type device making the following possible.
 - Reduction in the number of manufacturing processes for 2SJ268-applied equipment.
 - High density surface mount applications.
 - Small size of 2SJ268-applied equipment.

Absolute Maximum Ratings at $T_a = 25^\circ C$

			unit
Drain to Source Voltage	V_{DS}	-60	V
Gate to Source Voltage	V_{GS}	± 15	V
Drain Current(DC)	I_D	-18	A
Drain Current(Pulse)	I_{DP}	-72	A
Allowable Power Dissipation	P_D	1.65	W
		70	W
	$T_c = 25^\circ C$	150	$^\circ C$
Channel Temperature	T_{ch}	-55 to +150	$^\circ C$
Storage Temperature	T_{stg}		

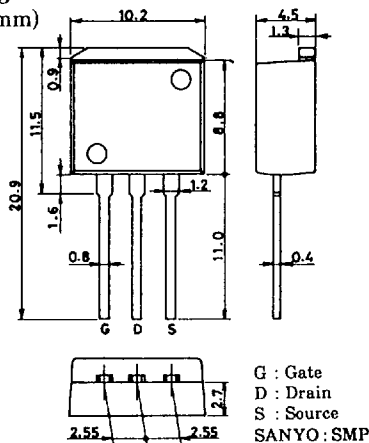
Electrical Characteristics at $T_a = 25^\circ C$

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0$	-60			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	± 15			V
Zero Gate Voltage	I_{DSS}	$V_{DS} = -60V, V_{GS} = 0$			-100	μA
Drain Current						
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.0		-2.0	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = -10V, I_D = -9A$	8	13.5		S
Static Drain to Source	$R_{DS(on)}$	$I_D = -9A, V_{GS} = -10V$		60	80	$m\Omega$
on State Resistance	$R_{DS(on)}$	$I_D = -9A, V_{GS} = -4V$		80	110	$m\Omega$

Continued on next page.

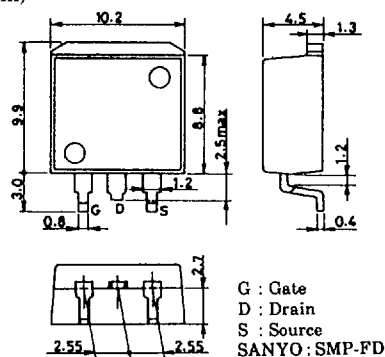
Package Dimensions 2093

(unit : mm)



Package Dimensions 2090

(unit : mm)



Continued from preceding page.

			min	typ	max	unit
Input Capacitance	C_{iss}	$V_{DS} = -20V, f = 1MHz$		1900		pF
Output Capacitance	C_{oss}	$V_{DS} = -20V, f = 1MHz$		600		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -20V, f = 1MHz$		150		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		18		ns
Rise Time	t_r	"		35		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		350		ns
Fall Time	t_f	"		250		ns
Diode Forward Voltage	V_{SD}	$I_S = -18A, V_{GS} = 0$	-1.0	-1.5		V

Switching Time Test Circuit

